Reg. No. :

Question Paper Code : 22093

B.E./B.Tech. DEGREE EXAMINATION, NOVEMBER/DECEMBER 2015.

Second Semester

Civil Engineering

PH 2161/PH 23/080040002 — ENGINEERING PHYSICS – II

(Common to all branches)

(Regulations 2008)

Time : Three hours

Maximum : 100 marks

Answer ALL questions.

PART A — $(10 \times 2 = 20 \text{ marks})$

1. State Wiedemann-Franz law.

- 2. Calculate the conductivity of intrinsic semiconductor if the mobilities of electrons and holes in it are $8.6 \times 10^6 \text{ m}^2/\text{v.s.}$ and $1.7 \times 10^6 \text{ m}^2/\text{v-s.}$ respectively. The electron and hole densities in the sample is $2.2 \times 10^{19}/\text{m}^3$.
- 3. Mention the drawbacks of classical free electron theory.
- 4. Distinguish between intrinsic and extrinsic semiconductors.
- 5. What are antiferro magnetic materials? Give examples.
- 6. What is magnetic levitation?
- 7. What is the effect of temperature on polarization in dielectrics?
- 8. What is thermal breakdown in dielectrics?
- 9. Mention some of the applications of shape memory alloys.
- 10. Write any four properties of Nanomaterials.

PART B — $(5 \times 16 = 80 \text{ marks})$

- 11. (a) (i) Derive the expressions for electrical and thermal conductivity based on classical free electron theory. (10)
 - (ii) Calculate the electrical and thermal conductivities for a metal with a relaxation time of 10^{-14} second at 300 K. Also calculate the Lorentz number using the above result. [Density of electrons 6×10^{28} /m³] (6)

Or

- (b) (i) Derive an expression for density of energy states. (10)
 - (ii) Give an account on Fermi-Dirac distribution function. Draw a graph showing its variation with energy at different temperature and discuss it.
 (6)

- (a) (i) Derive an expression for carrier concentration in intrinsic semiconductors. (10)
 - (ii) Explain in detail how the band gap energy of an intrinsic semiconductor is determined.
 (6)

Or

- (b) (i) Explain in detail the variation of Fermi level with temperature and impurity concentration in N type semiconductors. (10)
 - (ii) What is Hall effect? Obtain an expression for Hall coefficient. (6)
- 13.

(a)

12.

- (i) Explain the domain theory of Ferromagnetism and hence describe the magnetic hysteresis. (10)
- (ii) What are Ferrites? Explain magnetic recording and read out mechanisms.
 (6)

Or

- (b) (i) Describe the different properties of superconductors and also explain the classification of super conductors as Type I and Type II superconductors. (10)
 - (ii) Explain BCS theory of superconductors. (6)
- 14. (a) (i) Define Electrical susceptibility. Explain electronic, ionic, orientational and space charge polarization. (10)
 - (ii) Give an account on the use of dielectric materials in capacitors and transformers.
 (6)

Or

- (b) (i) What is internal field? Derive an expression for local field and hence obtain Clausius-Mosotti relation. (10)
 - (ii) Discuss the frequency dependence of polarization. (6)
- 15. (a) (i) What are metallic glasses? Explain the preparation, properties and applications of metallic glasses. (10)
 - (ii) What are nanomaterials? Explain the chemical vapour deposition method to synthesis nanomaterials.
 (6)

Or

- (b) (i) What are shape memory alloys? Discuss the characteristics and properties of shape memory alloys. (10)
 - (ii) Explain the pulsed laser deposition method of fabricating carbon Nanotubes. Mention some of the applications of carbon nanotubes.

(6)